Elektronische Bauelemente

PZTA44

200mA , 400V

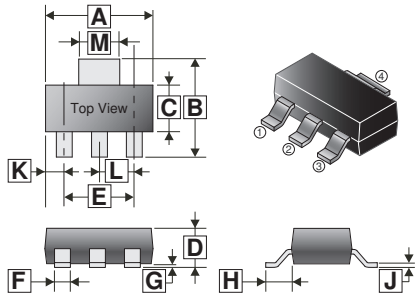
NPN Silicon Medium Power Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

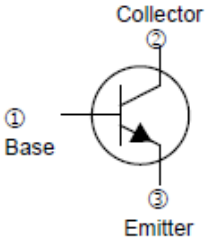
FEATURES

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage

SOT-223



REF.	Millimeter Min.	Millimeter Max.	REF.	Millimeter Min.	Millimeter Max.
A	6.20	6.70	G	-	0.10
B	6.70	7.30	H	-	-
C	3.30	3.70	J	0.25	0.35
D	1.42	1.90	K	-	-
E	4.50	4.70	L	2.30 REF.	
F	0.60	0.82	M	2.90	3.10



PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-223	2.5K	13' inch

ABSOLUTE MAXIMUM RATINGS (T_A = 25℃ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current -Continuous	I_C	200	mA
Collector Current -Pulsed	I_{CM}	300	mA
Collector Power Dissipation	P_C	1	W
Storage Temperature	T_{STG}	150, -65~150	℃

ELECTRICAL CHARACTERISTICS (T_A = 25℃ unless otherwise specified)

Parameter	Symbol	Min.	Max.	Unit	Test Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}$	400	-	V	I_C=0.1mA , I_E=0
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	400	-	V	I_C= 1mA, I_B=0
Emitter-base breakdown voltage	$V_{(BR)EBO}$	6	-	V	I_E= 100μA, I_C=0
Collector cut-off current	I_{CBO}	-	100	nA	V_{CB}= 400V, I_E=0
Emitter cut-off current	I_{EBO}	-	100	nA	V_{EB}= 4V, I_C=0
DC current gain[1]	h_{FE}	40	-		V_{CE}= 10V, I_C= 1mA
		50	200		V_{CE}= 10V, I_C= 10mA
		45	-		V_{CE}= 10V, I_C= 50mA
		40	-		V_{CE}= 10V, I_C= 100mA
Collector-emitter saturation voltage[1]	$V_{CE(sat)}$	-	0.4	V	I_C=1mA, I_B= 0.1mA
		-	0.5		I_C=10mA, I_B=1mA
		-	0.75		I_C=50mA, I_B=5mA
Base-emitter voltage	$V_{BE(on)}$	-	0.85	V	V_{CE}= 10V, I_C=1mA
Transition frequency	f_T	20	-	MHz	V_{CE}= 10V, I_C= 10mA, f=100MHz
Collector ca pacitance	C_C	-	7	pF	V_{CB}=20V, I_E=0, f=0MHz
Emitter capacitance	C_E	-	180	pF	V_{CB}=0.5V, I_E=0, f=0MHz